

## WHAT IS CLAIMED IS:

1. A method for manufacturing a liquid crystal panel of an active matrix system, comprising the steps of:

5 performing arraying for plotting a master glass substrate into a plurality of blocks, further plotting each block into one, alternatively a plurality of device-forming regions, and forming a conductive film, an insulating film and a semiconductor film which constitute TFT (Thin Film Transistor) in the device-forming region;

10 performing primary cutting for cutting the master glass substrate into the respective blocks to form a plurality of sub-TFT substrates;

15 performing sub-TFT substrate processing for executing processing for each sub-TFT substrate in accordance with a device to be manufactured; and

20 performing secondary cutting for cutting the sub-TFT substrate into each of the device-forming regions.

2. A manufacturing method of a liquid crystal panel according to claim 1, wherein only liquid crystal panels having identical sizes are formed in each block of the master glass substrate.

- 25 3. A manufacturing method of a liquid crystal panel according to claim 1, wherein two, alternatively more kinds of liquid crystal panels different from

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each other in size are formed in each block of the master glass substrate.

4. A manufacturing method of a liquid crystal panel according to claim 1, wherein said sub-TFT substrate processing step includes the steps of: forming a pixel electrode above the sub-TFT substrate; forming an orientation film for covering the pixel electrode; and joining a second substrate onto the sub-TFT substrate, and after the secondary cutting step, a step of sealing a liquid crystal between the sub-TFT substrate and the second substrate after the cutting is provided.
5. A manufacturing method of a liquid crystal panel according to claim 1, wherein said arraying step includes the steps of: forming an amorphous silicon film above the master glass substrate; and converting the amorphous silicon film into a polysilicon film by irradiating the amorphous silicon film with a rectangular laser beam and moving the laser beam in one direction.
6. A manufacturing method of a liquid crystal panel according to claim 1, wherein said sub-TFT substrate processing step includes at least one of the steps of: performing corner cutting for the sub-TFT substrate after the primary cutting; and performing end face processing for the same after

the primary cutting.

5 7. A manufacturing method of a liquid crystal panel according to claim 1, wherein for forming liquid crystal panels having united driving circuit of plural kinds and different size by using the master glass substrate, arranging directions of the driving circuits are identical to one another with respect to a display section of each liquid crystal panel.

*delay the circuit steps*

10 8. A manufacturing method of a liquid crystal panel according to claim 1, wherein in said sub-TFT substrate processing step, pattern alignment is performed by using a fiducial mark provided for each sub-TFT substrate.

15 9. A manufacturing method of a liquid crystal panel according to claim 1, wherein said sub-TFT substrate processing step includes a step of forming a semiconductor film above the sub-TFT substrate.

20 10. A manufacturing method of a liquid crystal panel according to claim 9, wherein in at least one of the plurality of blocks, a photoelectric conversion element using the semiconductor film is formed.

25 11. A manufacturing method of a liquid crystal panel according to claim 1, wherein direct-vision liquid crystal panels are formed in all of the plurality of device-forming regions.

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12. A manufacturing method of a liquid crystal panel according to claim 1, wherein direct-vision liquid crystal panels are formed in the plurality of device-forming regions, and a projection panel type is formed in the other device-forming region.
13. A manufacturing method of a liquid crystal panel according to claim 1, wherein a liquid crystal panel of a transmission type is formed in a part of the plurality of device-forming regions, and a projection panel of a reflection type is formed in the other device-forming region.
14. A manufacturing method of a liquid crystal panel according to claim 1, wherein in at least one of the plurality of device-forming regions, a liquid crystal panel with a built-in image sensor is formed.
15. A liquid crystal panel formed by a process comprising the steps of:
- forming a conductive film, an insulating film and a semiconductor film which constitute TFT on a master glass substrate;
- performing primary cutting for the master glass substrate to be divided into a plurality of sub-TFT substrates;
- forming a pixel electrode and a first orientation film in a state of the sub-TFT substrate;
- joining a color filter substrate having a color

filter, a counter electrode and a second orientation film to the sub-TFT substrate; and sealing a liquid crystal between the sub-TFT substrate and the color filter substrate after performing secondary cutting for the sub-TFT substrate.

16. A manufacturing system of a liquid crystal panel comprising:

a first manufacturing line including a plurality of manufacturing equipment for plotting a master glass substrate into a plurality of blocks, further plotting each block into one, alternatively a plurality of device-forming regions, and forming TFT in at least one of the device-forming regions; and

a second manufacturing line including a plurality of manufacturing equipment for executing processing for a sub-TFT substrate after primary cutting process in accordance with a device to be manufactured, said sub-TFT substrate being one of a plurality of sub-TFT substrates obtained by dividing the master glass substrate into the respective blocks.

17. A manufacturing system of a liquid crystal panel according to claim 16, wherein said first manufacturing line includes a film-forming equipment for forming a semiconductor film serving

as an active layer of TFT, and said second manufacturing line includes a film-forming equipment for forming a pixel electrode.

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